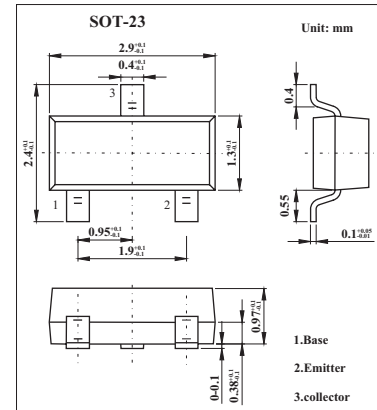


NPN Transistor 2SC3052

■ Features

- Collector current : $I_C=0.2A$
- Power dissipation : $P_C=0.15W$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	50	V
Collector-emitter voltage	V_{CE0}	50	V
Emitter-base voltage	V_{EB0}	6	V
Collector current	I_C	200	mA
power dissipation *	P_C	150	mW
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

*. 0.7 mmx16 cm² ceramic substrate

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_C = 100 \mu A, I_E = 0$	50			V
Collector-emitter breakdown voltage	V_{CE0}	$I_C = 100 \mu A, I_B = 0$	50			V
Emitter-base breakdown voltage	V_{EB0}	$I_E = 100 \mu A, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 50V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 6V, I_C = 0$			0.1	μA
DC current gain	hFE	$V_{CE} = 6V, I_C = 1mA$	150		800	
		$V_{CE} = 6V, I_C = 0.1mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 10mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 100mA, I_B = 10mA$			1	V
Collector output capacitance	C_{ob}	$V_{CE} = 6V, I_E = 0, f = 1MHz$			4	pF
Noise figure	NF	$V_{CE} = 6V, I_E = -0.1mA, f = 1KHz, R_G = 2K \Omega$			15	dB
Transition frequency	f_T	$V_{CE} = 6V, I_C = 10mA$	180			MHz

■ hFE Classification

Marking	LE	LF	LG
Rank	E	F	G
hFE	150 to 300	250 to 500	400 to 800